2SD2134

Silicon NPN epitaxial planar type

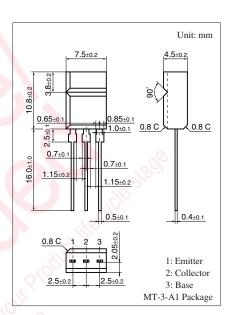
For low-frequency driver, high power amplification Complementary to 2SB1414

■ Features

- Excellent collector current I_C characteristics of forward current transfer ratio h_{FE}
- High transition frequency f_T
- A complementary pair with 2SB1414, is optimum for the driverstage of a 60 W to 100 W output amplifier.

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V_{CBO} | 150 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | 150 | V | |
| Emitter-base voltage (Collector open) | V_{EBO} | 5 | V | |
| Collector current | I_{C} | 1 | A | |
| Peak collector current | I_{CP} | 1.5 | A | |
| Collector power dissipation | P _C | 1.5 | W | |
| Junction temperature | T_{j} | 150 | °°C | |
| Storage temperature | T_{stg} | -55 to +150 | S °C | |
| | | | | |



■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

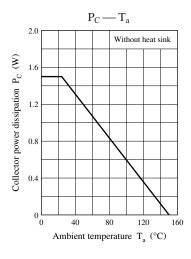
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---------------------------------------|----------------------|--|-----|-----|-----|------|
| Collector-emitter voltage (Base open) | V_{CEO} | $I_C = 100 \mu\text{A}, I_B = 0$ | 150 | | | V |
| Emitter-base voltage (Collector open) | $V_{\rm EBO}$ | $I_E = 10 \mu\text{A}, I_C = 0$ | 5 | | | V |
| Forward current transfer ratio | h _{FE1} * | V _{CE} = 10 V, I _C = 150 mA | 90 | | 220 | _ |
| | h _{FE2} | $V_{CE} = 5 \text{ V}, I_{C} = 500 \text{ mA}$ | 50 | | | |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | | 0.5 | 2.0 | V |
| Base-emitter saturation voltage | V _{BE(sat)} | $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | | 1.0 | 2.0 | V |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$ | | 200 | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$ | | 20 | | pF |
| (Common base, input open circuited) | | 16.0. Krz. | | | | |

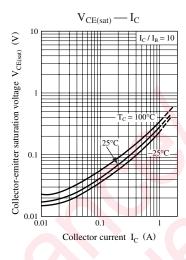
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

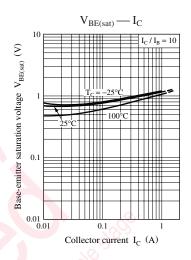
2. *: Rank classification

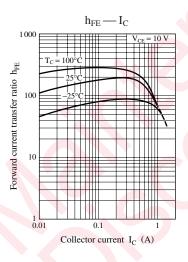
| Rank | Q | R |
|------------------|-----------|------------|
| h _{FE1} | 90 to 155 | 130 to 220 |

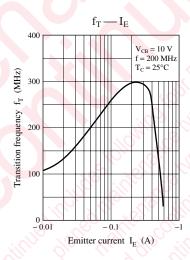
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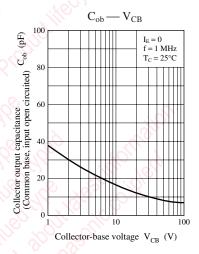


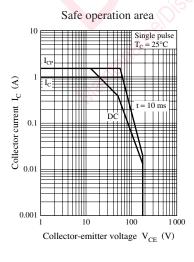


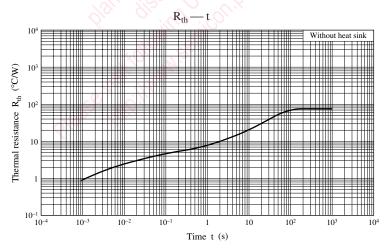












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